

PJQ5512S6C-AU

25V N-Channel Enhancement Mode MOSFET

Voltage

25 V

Current

550 A

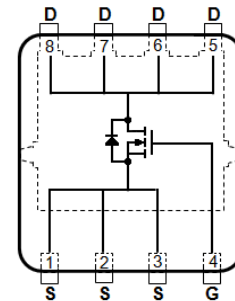
Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A < 0.59m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@20A < 0.94m\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060XC-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.098 grams

DFN5060XC-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	25	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^(Note 3)	$T_C=25^\circ\text{C}$	I_D	550	A
	$T_C=100^\circ\text{C}$		389	
Pulsed Drain Current ^(Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	990	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	268	W
	$T_C=100^\circ\text{C}$		134	
Continuous Drain Current ^(Note 4)	$T_A=25^\circ\text{C}$	I_D	65	A
	$T_A=70^\circ\text{C}$		55	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	3.8	W
	$T_A=70^\circ\text{C}$		2.6	
Single Pulse Avalanche Current ^(Note 6)		I_{AS}	32	A
Single Pulse Avalanche Energy ^(Note 6)		E_{AS}	378	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~175	$^\circ\text{C}$
Thermal Resistance	Junction to Case	$R_{\theta JC}$	0.56	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$ ^(Note 4)	40	
		$R_{\theta JA}$ ^(Note 5)	26(Typ.)	

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	25	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.2	1.6	2.2	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	0.47	0.59	mΩ
		V _{GS} =4.5V, I _D =20A	-	0.72	0.94	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =25V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	122	160	nC
Gate-Source Charge	Q _{gs}		-	14.5	-	
Gate-Drain Charge	Q _{gd}		-	24	-	
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f=1MHz	-	7437	9700	pF
Output Capacitance	C _{oss}		-	2980	3880	
Reverse Transfer Capacitance	C _{rss}		-	161	250	
Gate resistance	R _g	f=1MHz	-	3.3	-	Ω
Turn-On Delay Time	td _(on)	V _{DS} =20V, I _D =20A, V _{GS} =10V, R _G =3Ω (Note 2)	-	12	-	ns
Turn-On Rise Time	tr		-	27	-	
Turn-Off Delay Time	td _(off)		-	129	-	
Turn-Off Fall Time	tf		-	84	-	
Drain-Source Diode						
Diode Forward Current	I _S	T _C =25°C (Package Limit)	-	-	302	A
Pulsed Diode Forward Current	I _{SM}		-	-	990	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.73	1.3	V
Reverse Recovery Time	T _{rr}	V _{DD} =20V, V _{GS} =0V,	-	72	-	ns
Reverse Recovery Charge	Q _{rr}	I _S =20A, dI _S /dt=100A/us	-	82	-	nC

NOTES :

- Pulse width≤100us, Duty cycle≤2%.
- Essentially independent of operating temperature typical characteristics.
- Chip capability with an R_{θJC}=0.56°C/W, Pakage limited 120A.
- R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5,-7) PCB is vertical in still air.
- E_{AS} is calculated based on the condition of L=1mH, I_{AS}=27.5A, V_{DD}=30V, V_{GS}=10V. 100% test at L=0.5mH, I_{AS}=32A in production.
- Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

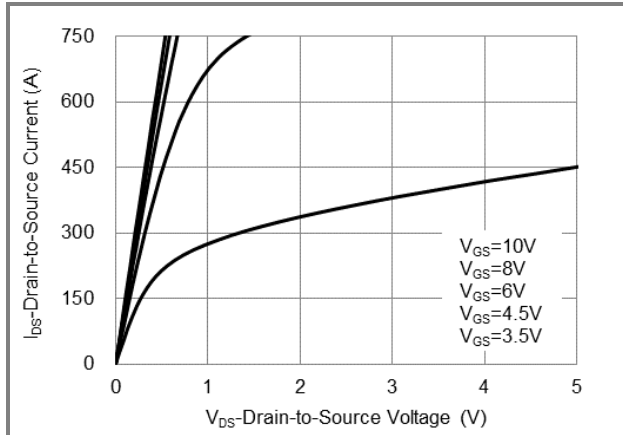


Fig.1 On-Region Characteristics

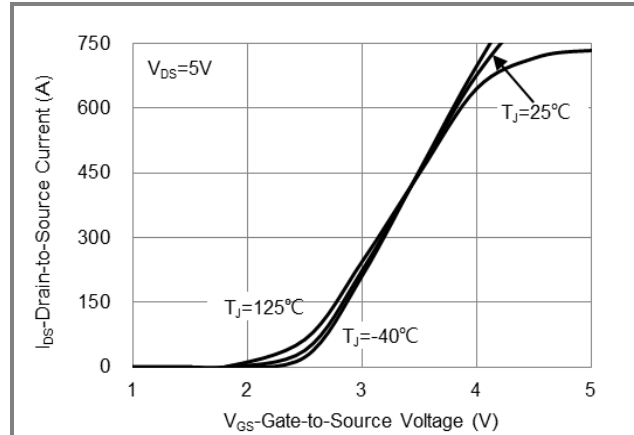


Fig.2 Transfer Characteristics

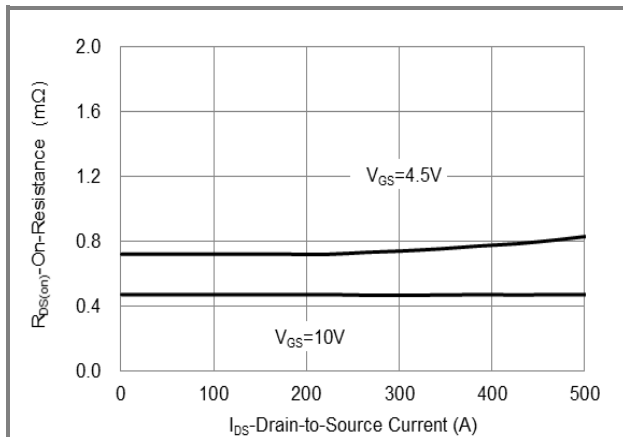


Fig.3 On-Resistance vs. Drain Current

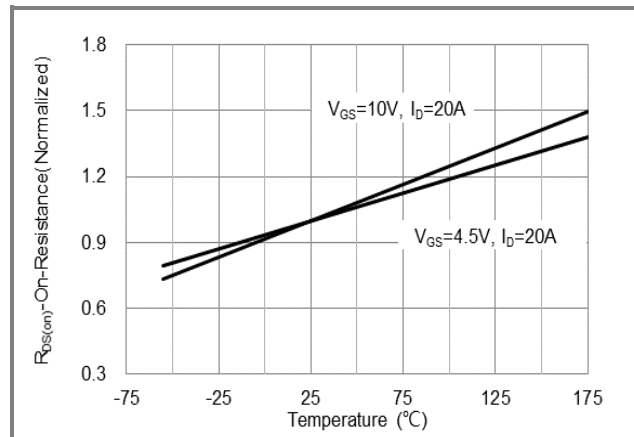


Fig.4 On-Resistance vs. Junction temperature

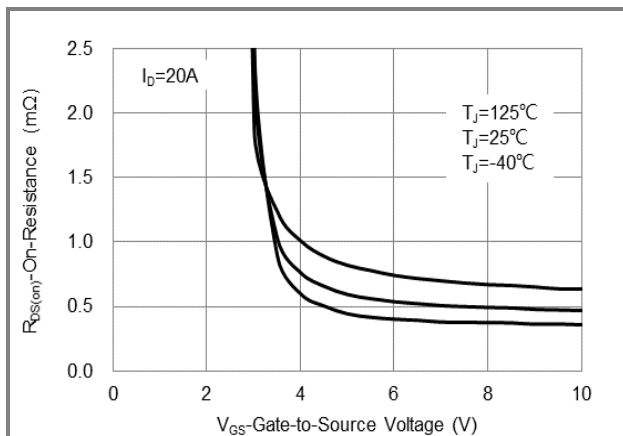


Fig.5 On-Resistance Variation with V_{GS}

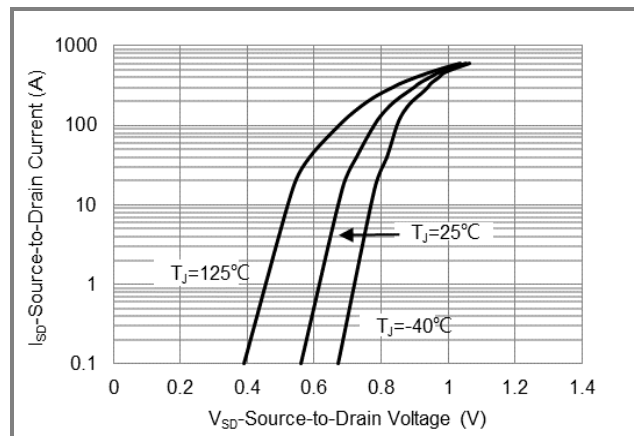
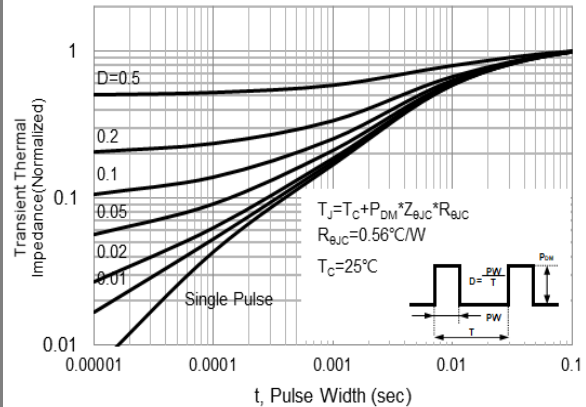
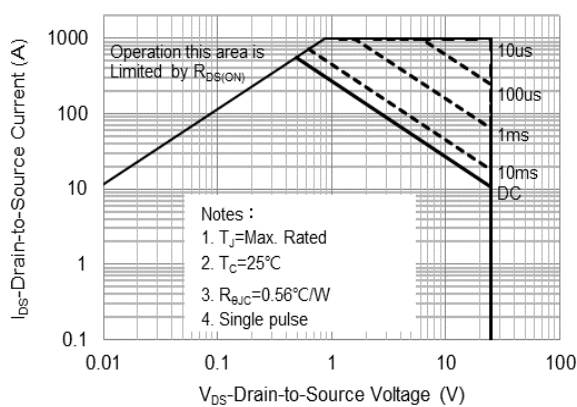
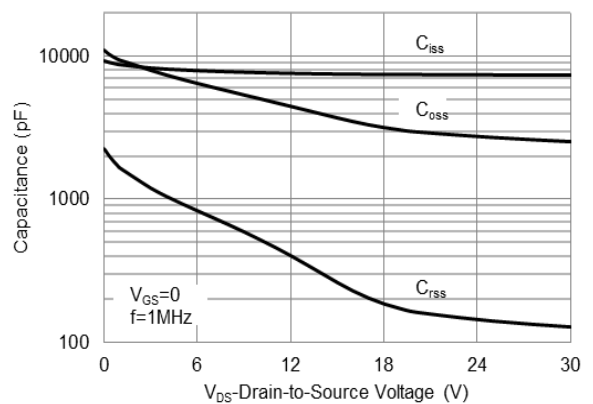
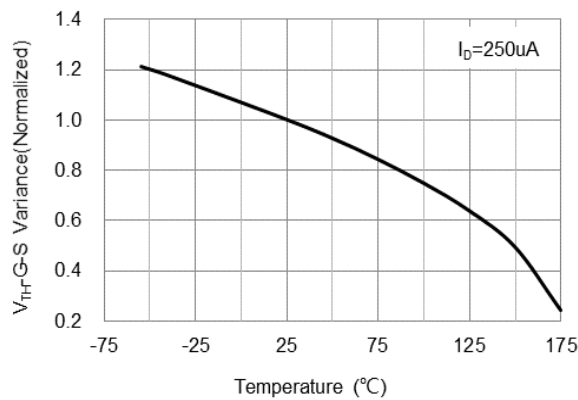
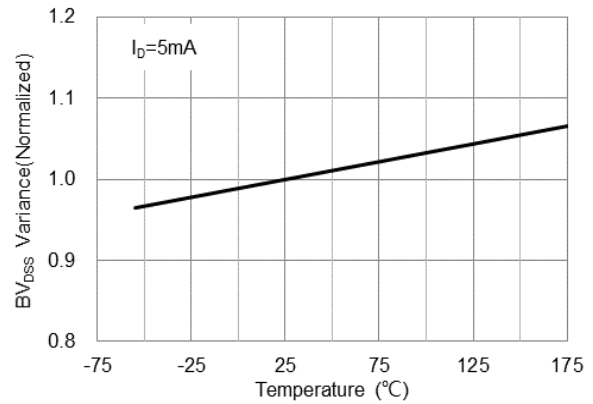
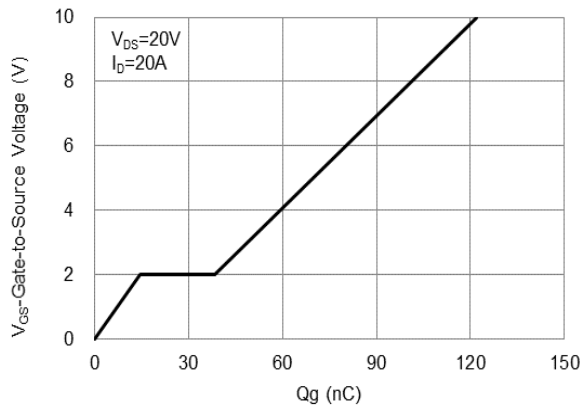


Fig.6 Source-Drain Diode Forward Voltage

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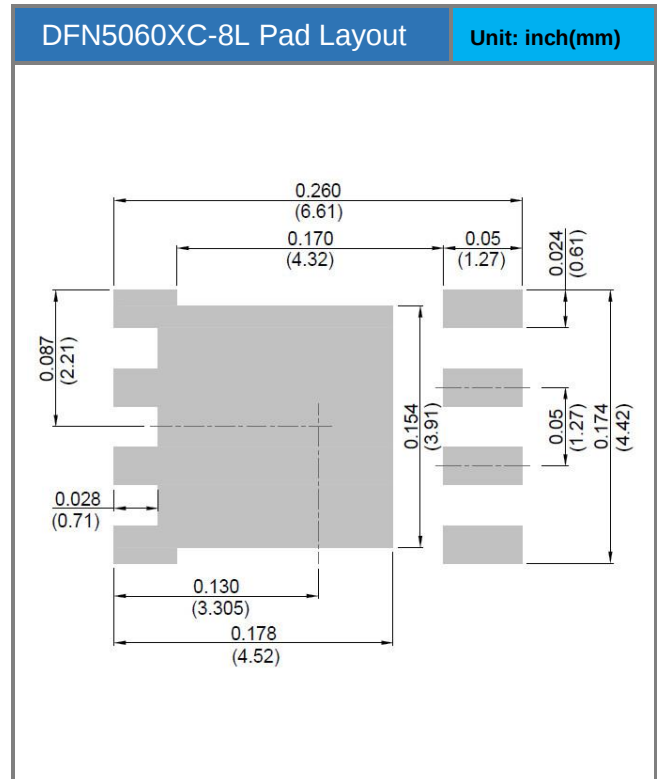
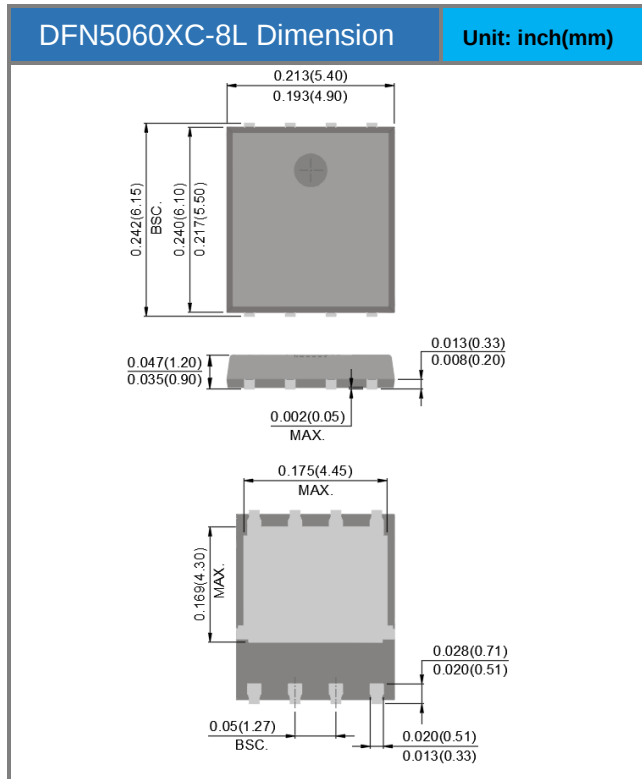


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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ5512S6C-AU	DFN5060XC-8L	3K pcs / 13" reel	5512S6C

Packaging Information & Mounting Pad Layout



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